

Amendments to the Specification

Please amend the paragraph beginning at page 16, line 15 as follows:

Following formation of emitter tip 64, further processing may be carried out in order to construct, in the vicinity of emitter tip 64, structures that enable an electric field to be applied to emitter tip 64 such that an electron flux is emitted therefrom. It will be understood that any of a number of structures and corresponding processes may be used according to the invention to form the aforementioned structures in the vicinity of emitter tip 64. For example, Figure 7 illustrates a partial cross section of a completed flat panel display that includes emitter tip 64 as part of a field emission device. It may be noted that the structure of Figure 7 is substantially similar in many aspects to the structure of Figure 1, with the marked difference of the substantial rectilinearity of emitter tip 64 of Figure 7, which is a result of the inventive method. Similarly, Figure 8 illustrates a partial cross section of a completed flat panel display that includes a substantially rectilinear emitter tip 64. In the embodiment depicted in Figure 8, it can be seen that the emitter tip 64 is integrally formed with the emitter layer 120, which is disposed over cathode conductive layer 80, which is in turn disposed over substrate 52, as part of the field emission device. As previously noted, however, the cathode conductive layer 80, the emitter layer 120, and the emitter tip 64 are each formed from substrate 52 by various etching and implanting steps. Thus, the cathode conductive layer 80 and the emitter layer 120 may not be clearly delineated layers in the event that the implanting step that forms the cathode conductive layer implants in the region of the emitter layer. Nevertheless, for clarity in describing the invention the layers are presented in Figure 8 as discrete layers.

Please amend the paragraph beginning at page 17, line 7 as follows:

While as few as one emitter tip 64 may be formed, in practice, it is common to form an array of as many as tens of millions or more of emitter tips 64 over a substrate 52. The formation of emitter tip 64 as illustrated in Figure 6 and 7, such that wings have been avoided and emitter tip 64 has a substantially rectilinear vertical profile, provides a geometry that is highly efficient for generating an electron flux. In particular, the localized work function of the material that constitutes emitter tip 64 is relatively low at the apex of the emitter tip 64. As a result, a relatively high electron flux 86 can be generated from a given voltage, and electron emission will be substantially limited to the apex.